

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

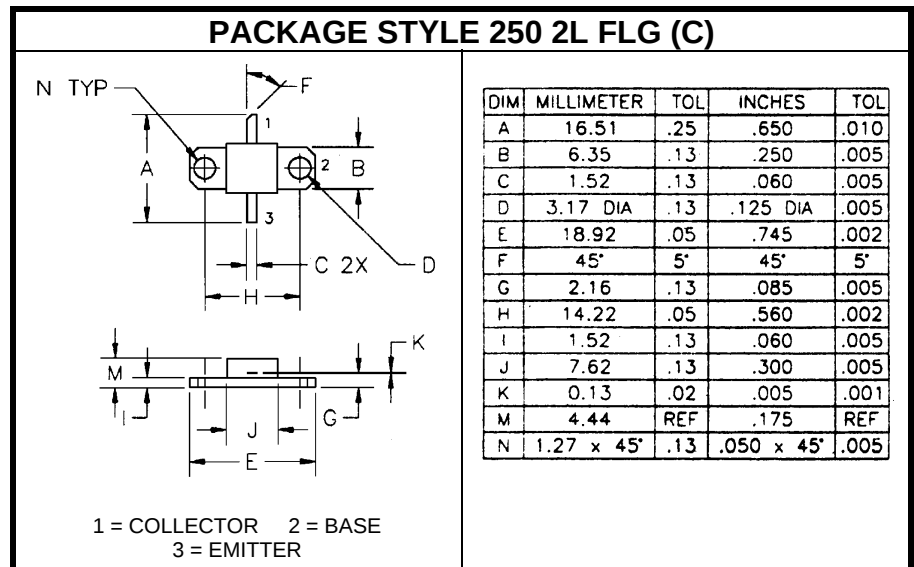
The **ASI MRA1417-11** is a Common Base Device Designed for Class C Power Amplifier Applications up to 1.7 GHz.

FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	50 V
P_{DISS}	12 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$
θ_{JC}	$4.5^\circ C/W$



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 80 \text{ mA}$	50			V
BV_{EBO}	$I_E = 1.0 \text{ mA}$	3.5			V
I_{CBO}	$V_{CB} = 28 \text{ V}$			2.0	mA
h_{FE}	$V_{CE} = 5.0 \text{ V}$ $I_C = 4.0 \text{ A}$	10		100	---
C_{ob}	$V_{CB} = 28 \text{ V}$ $f = 1.0 \text{ MHz}$			12	pF
P_G	$V_{CE} = 28 \text{ V}$ $P_{OUT} = 11 \text{ W}$ $f = 1700 \text{ MHz}$	7.4			dB
η_C		45			%